

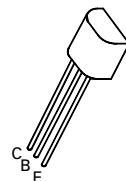
# PNP SILICON PLANAR MEDIUM POWER HIGH CURRENT TRANSISTOR

## ZTX955

ISSUE 3 – JUNE 94

### FEATURES

- \* 3 Amps continuous current
- \* Up to 10 Amps peak current
- \* Very low saturation voltage
- \* Excellent gain characteristics up to 3 Amps
- \* Spice model available



E-Line  
TO92 Compatible

### ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	$V_{CBO}$	-180	V
Collector-Emitter Voltage	$V_{CEO}$	-140	V
Emitter-Base Voltage	$V_{EBO}$	-6	V
Peak Pulse Current	$I_{CM}$	-10	A
Continuous Collector Current	$I_C$	-3	A
Practical Power Dissipation*	$P_{totp}$	1.58	W
Power Dissipation at $T_{amb}=25^{\circ}C$	$P_{tot}$	1.2	W
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +200	$^{\circ}C$

\*The power which can be dissipated assuming the device is mounted in a typical manner on a P.C.B. with copper equal to 1 inch square minimum

### ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-180	-210		V	$I_C = -100\mu A$
Collector-Emitter Breakdown Voltage	$V_{(BR)CER}$	-180	-210		V	$I_C = -1\mu A, R_B \leq 1K\Omega$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-140	-170		V	$I_C = -10mA^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-6	-8		V	$I_E = -100\mu A$
Collector Cut-Off Current	$I_{CBO}$			-50 -1	nA $\mu A$	$V_{CB} = -150V$ $V_{CB} = -150V, T_{amb} = 100^{\circ}C$
Collector Cut-Off Current	$I_{CER}$ $R \leq 1K\Omega$			-50 -1	nA $\mu A$	$V_{CB} = -150V$ $V_{CB} = -150V, T_{amb} = 100^{\circ}C$
Emitter Cut-Off Current	$I_{EBO}$			-10	nA	$V_{EB} = -6V$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-30 -60 -90 -250	-60 -100 -120 -330	mV mV mV mV	$I_C = -100mA, I_B = -5mA^*$ $I_C = -500mA, I_B = -50mA^*$ $I_C = -1A, I_B = -100mA^*$ $I_C = -3A, I_B = -300mA^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-920	-1050	mV	$I_C = -3A, I_B = -300mA^*$

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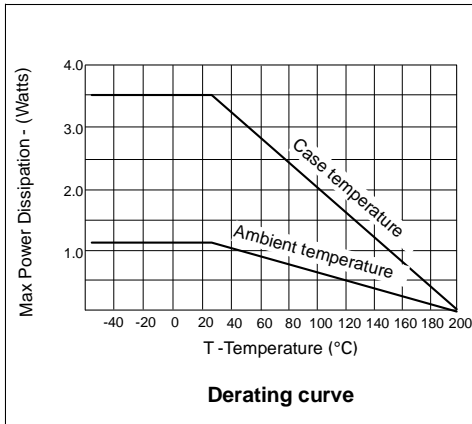
## ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ )

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		-790	-900	mV	$I_C = -3A, V_{CE} = -5V^*$
Static Forward Current Transfer Ratio	$h_{FE}$	100 100 75	200 200 140 10	300		$I_C = -10mA, V_{CE} = -5V^*$ $I_C = -1A, V_{CE} = -5V^*$ $I_C = -3A, V_{CE} = -5V^*$ $I_C = -10A, V_{CE} = -5V^*$
Transition Frequency	$f_T$		110		MHz	$I_C = -100mA, V_{CE} = -10V$ $f = 50MHz$
Output Capacitance	$C_{obo}$		40		pF	$V_{CB} = -20V, f = 1MHz$
Switching Times	$t_{on}$ $t_{off}$		68 1030		ns ns	$I_C = -1A, I_{B1} = -100mA$ $I_{B2} = -100mA, V_{CC} = -50V$

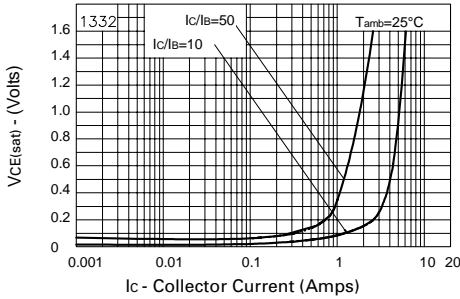
\*Measured under pulsed conditions. Pulse width=300 $\mu$ s. Duty cycle  $\leq$ 2%

## THERMAL CHARACTERISTICS

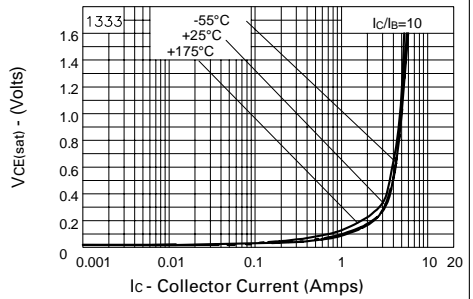
PARAMETER	SYMBOL	MAX.	UNIT
Thermal Resistance: Junction to Ambient Junction to Case	$R_{th(j-amb)}$ $R_{th(j-case)}$	150 50	$^{\circ}\text{C/W}$ $^{\circ}\text{C/W}$



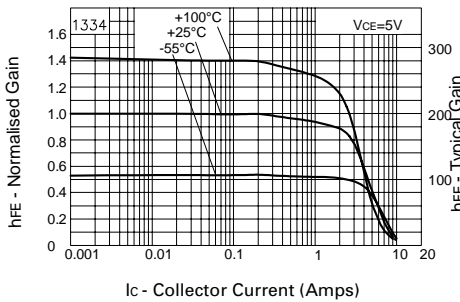
## TYPICAL CHARACTERISTICS



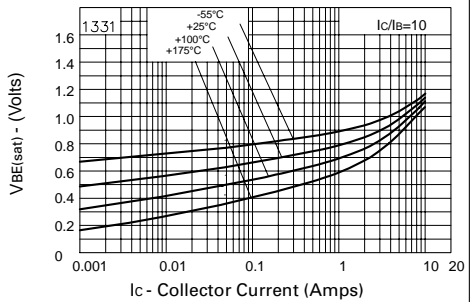
**$V_{CE(sat)}$  v  $I_C$**



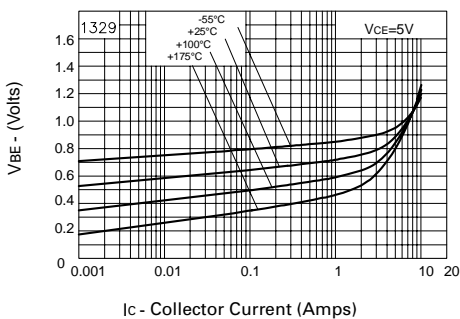
**$V_{CE(sat)}$  v  $I_C$**



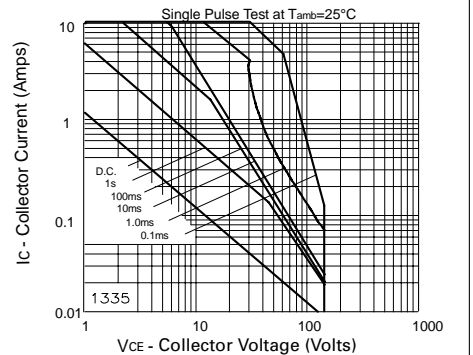
**$h_{FE}$  v  $I_C$**



**$V_{BE(sat)}$  v  $I_C$**



**$V_{BE(on)}$  v  $I_C$**



**Safe Operating Area**

单击下面可查看定价，库存，交付和生命周期等信息

[>>Diodes Incorporated\(达达科技\(美台\)\)](#)